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PATENT & TRADEMARK OFFICE
TC 2100

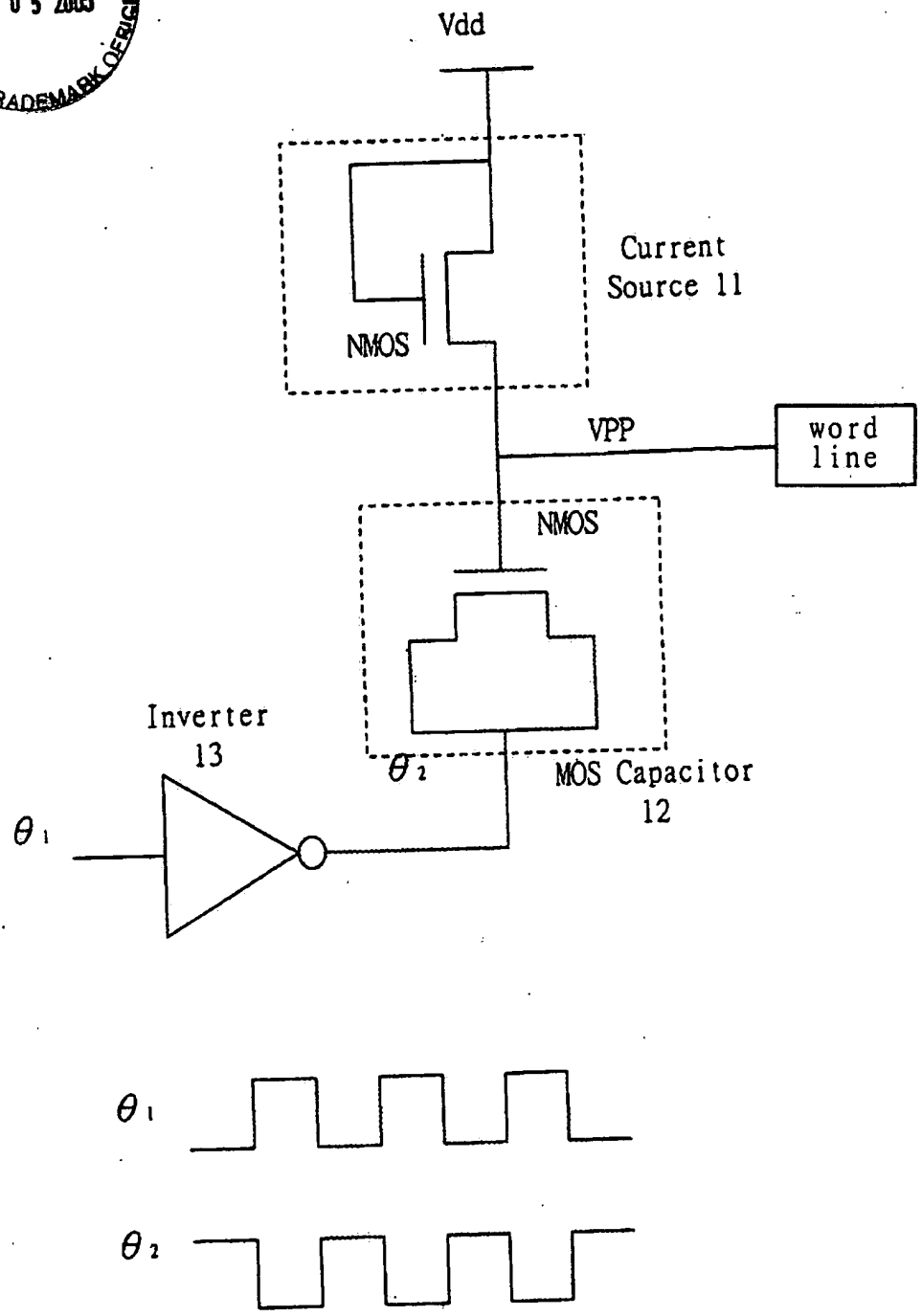

Figure 1 (Prior Art)

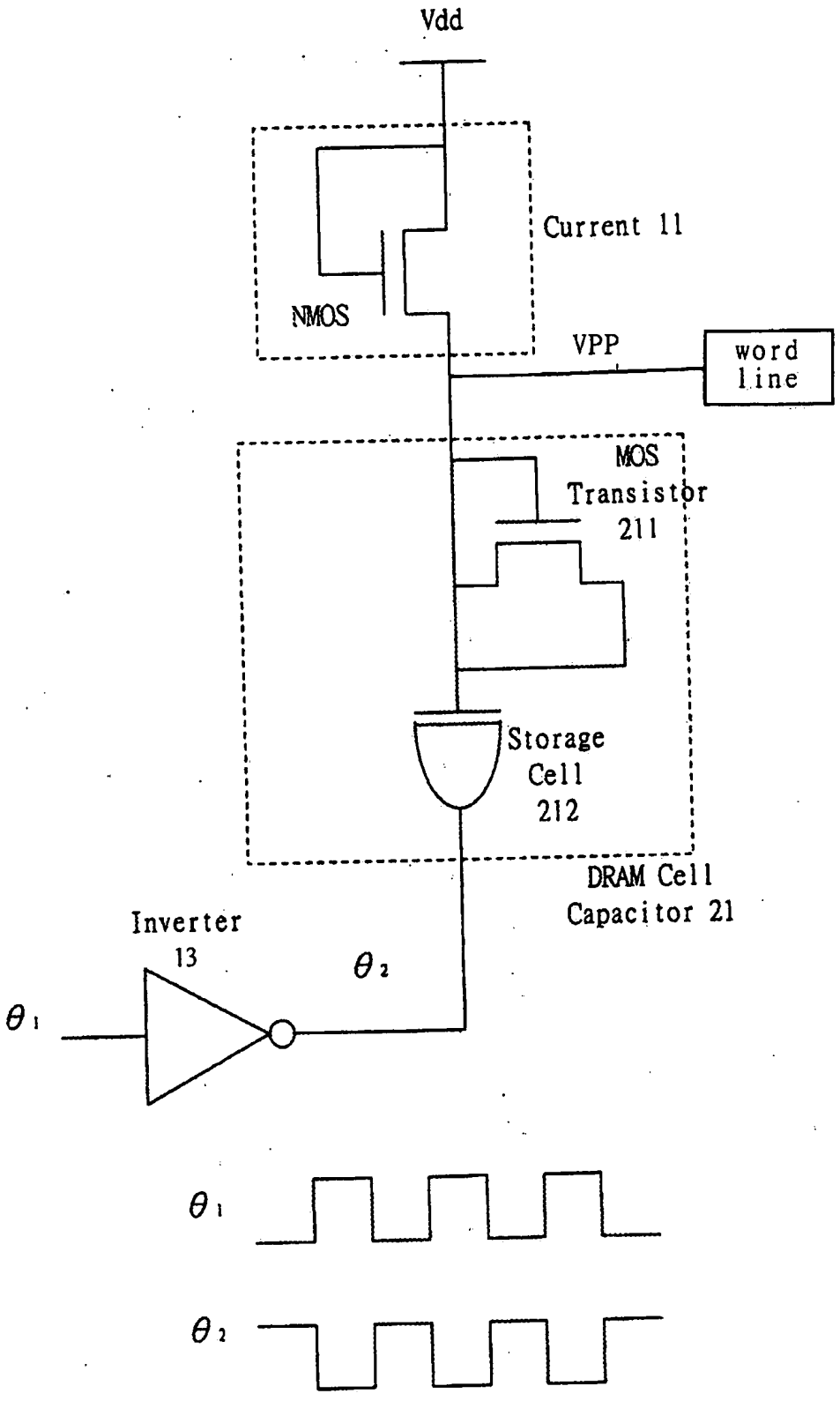
Vdd
Current 11
NMOS
VPP
word line
MOS Transistor 211
Storage Cell 212
DRAM Cell Capacitor 21
Inverter 13
θ2
θ1
θ1
θ2

Figure 2(A)

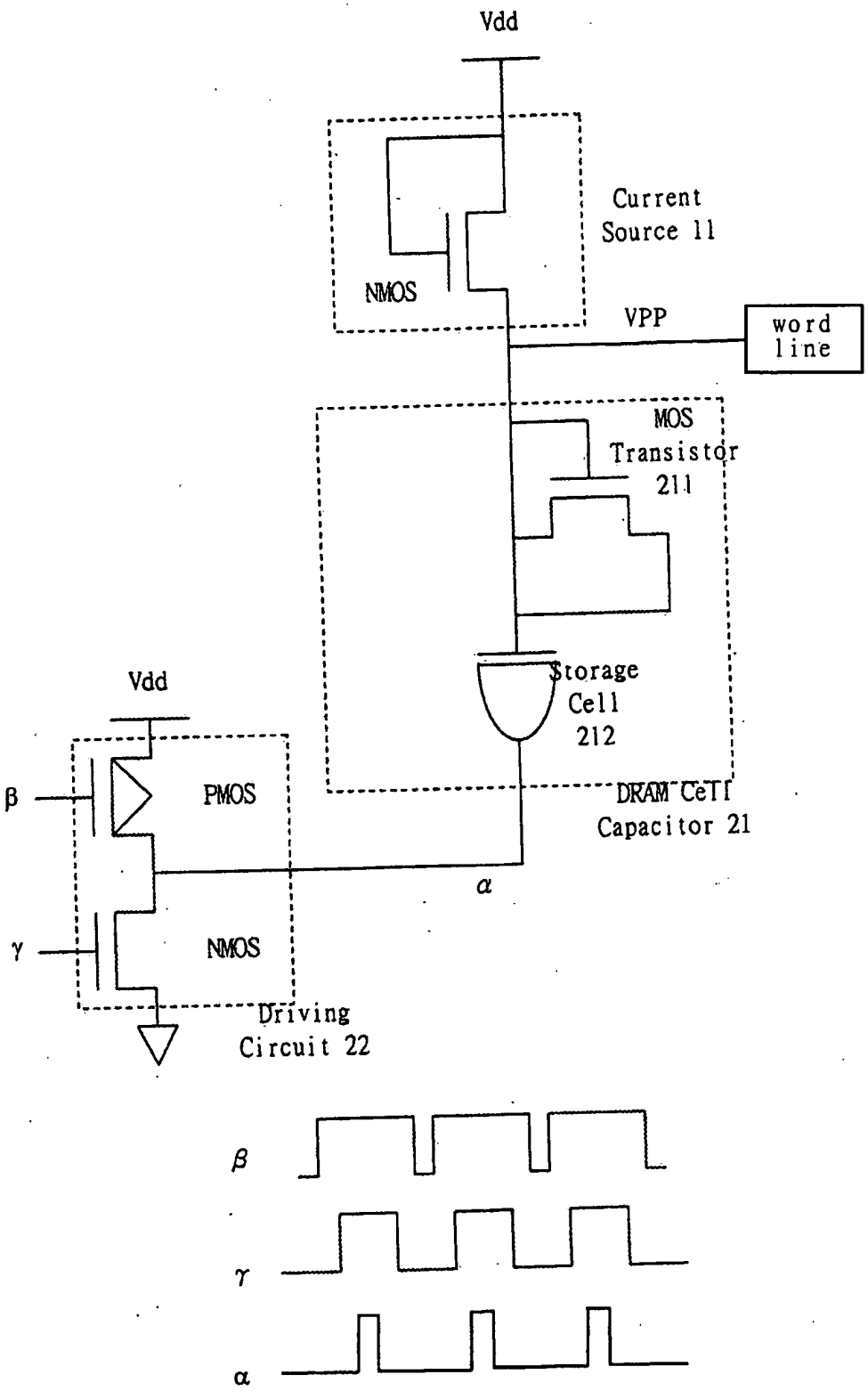
Vdd
Current
Source 11
NMOS
VPP
word
line
MOS
Transistor
211
Storage
Cell
212
DRAM Cell
Capacitor 21
Vdd
β
PMOS
α
γ
NMOS
Driving
Circuit 22
β
γ
α

Figure 2 (B)